

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

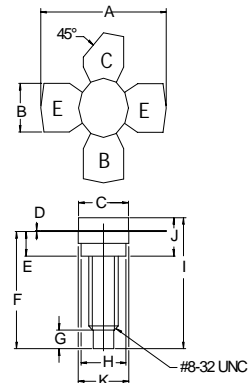
The **ASI BLW80** is Designed for Class A,B or C UHF & VHF Communication applications up to 470 MHz.

**FEATURES:**

- $P_G = 8.0$  dB Typical at 470 MHz
- **Omnigold™** Metallization System

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CES}$	36 V
$P_{DISS}$	17 W @ $T_C = 25\text{ }^\circ\text{C}$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	10.3 °C/W

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	17			V
$BV_{CES}$	$I_C = 10$ mA $V_{BE} = 0$ V	36			V
$BV_{EBO}$	$I_E = 4.0$ mA	4			V
$I_{CES}$	$V_{CE} = 17$ V			4.0	mA
$h_{FE}$	$V_{CE} = 5$ V $I_C = 5.0$ A	10	35		---
$V_{CE}$	$I_C = 1.5$ A $I_B = 300$ mA		0.75		V
$C_C$	$V_{CB} = 12.5$ V $F = 1.0$ MHz		14		pF
$P_G$	$V_{CE} = 12.5$ V $P_{OUT} = 4.0$ W $F = 470$ MHz	8.0	15		DB
$\eta$		60			%